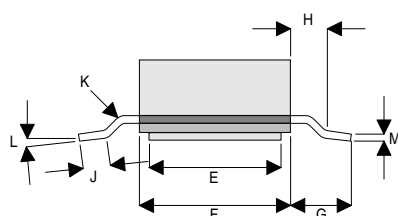
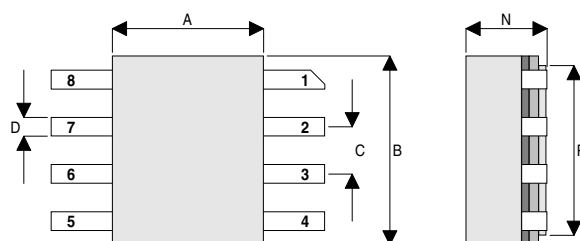


MECHANICAL DATA



SO8 PACKAGE

PIN 1 – SOURCE PIN 5 – SOURCE
 PIN 2 – DRAIN PIN 6 – GATE
 PIN 3 – DRAIN PIN 7 – GATE
 PIN 4 – SOURCE PIN 8 – SOURCE

Dim.	mm	Tol.	Inches	Tol.
A	4.06	±0.08	0.160	±0.003
B	5.08	±0.08	0.200	±0.003
C	1.27	±0.08	0.050	±0.003
D	0.51	±0.08	0.020	±0.003
E	3.56	±0.08	0.140	±0.003
F	4.06	±0.08	0.160	±0.003
G	1.65	±0.08	0.065	±0.003
H	0.76	+0.25 -0.00	0.030	+0.010 -0.000
J	0.51	Min.	0.020	Min.
	1.02	Max.	0.040	Max.
K	45°	Max.	45°	Max.
	0°	Min.	0°	Min.
L	7°	Max.	7°	Max.
	0.20	±0.08	0.008	±0.003
M	0.20	±0.08	0.008	±0.003
N	2.18	Max.	0.086	Max.
P	4.57	±0.08	0.180	±0.003

**GOLD METALLISED
 MULTI-PURPOSE SILICON
 DMOS RF FET
 10W – 28V – 500MHz
 SINGLE ENDED**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 13 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
 from 1 MHz to 1GHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	30W
BV_{DSS}	Drain – Source Breakdown Voltage	70V
BV_{GSS}	Gate – Source Breakdown Voltage	±20V
$I_{D(sat)}$	Drain Current	5A
T_{stg}	Storage Temperature	-65 to 150°C
T_j	Maximum Operating Junction Temperature	200°C

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS} Drain–Source Breakdown Voltage	V _{GS} = 0 I _D = 100mA	70			V
I _{DSS} Zero Gate Voltage Drain Current	V _{DS} = 28V V _{GS} = 0			1	mA
I _{GSS} Gate Leakage Current	V _{GS} = 20V V _{DS} = 0			1	μA
V _{GS(th)} Gate Threshold Voltage*	I _D = 10mA V _{DS} = V _{GS}	1		7	V
g _{fs} Forward Transconductance*	V _{DS} = 10V I _D = 1A	0.8			S
G _{PS} Common Source Power Gain	P _O = 10W	13			dB
η Drain Efficiency	V _{DS} = 28V I _{DQ} = 0.1A	50			%
VSWR Load Mismatch Tolerance	f = 500MHz	20:1			—
C _{iss} Input Capacitance	V _{DS} = 28V V _{GS} = -5V f = 1MHz			60	pF
C _{oss} Output Capacitance	V _{DS} = 28V V _{GS} = 0 f = 1MHz			30	pF
C _{rss} Reverse Transfer Capacitance	V _{DS} = 28V V _{GS} = 0 f = 1MHz			2.5	pF
R _{dson} Saturation Resistance	V _{GS} = 20V I _{DS} = 2.5A		1		Ω

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 6°C / W
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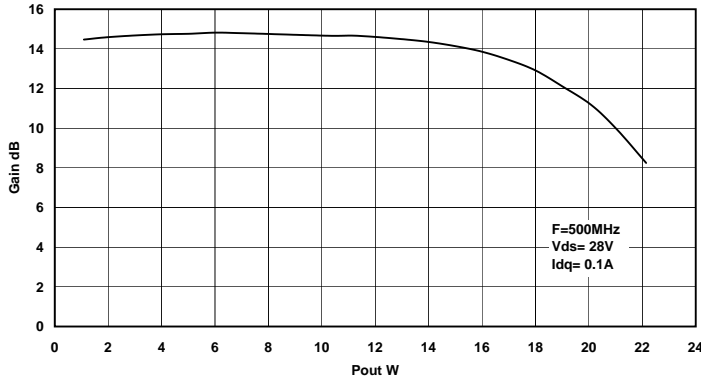


Figure 1
Gain vs. Output Power

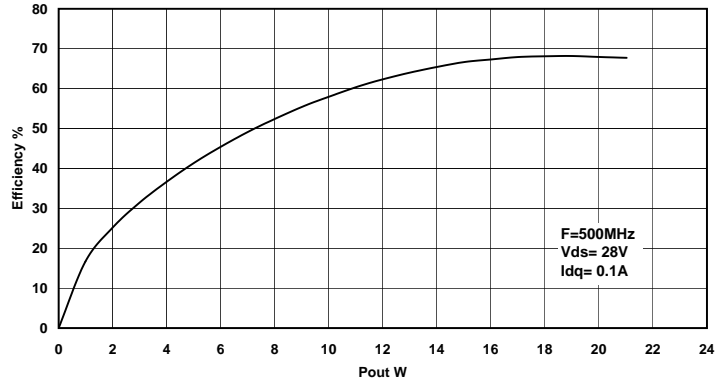


Figure 2
Power added efficiency vs. Output Power.

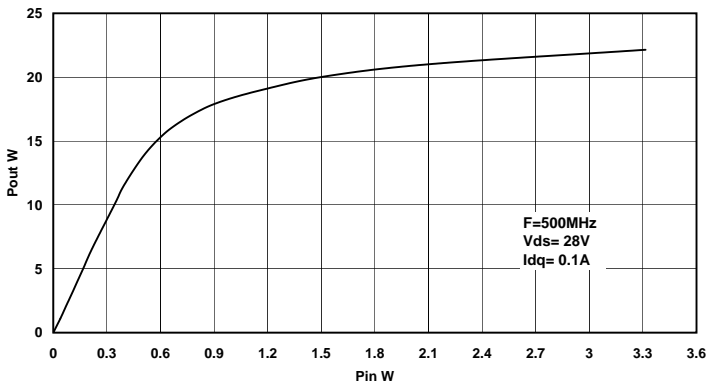


Figure 3
Output Power vs. Input Power.

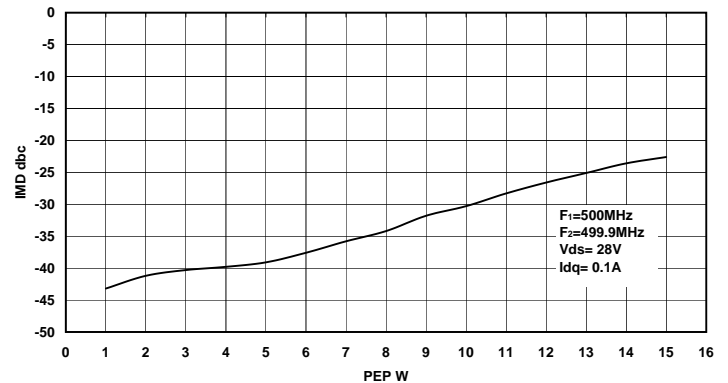


Figure 4
IMD 3 vs. PEP

Typical S Parameters

!D1011UK.s2p
!Vds=28V,Idq=0.1A
MHZ S MA R 50

Freq MHz	S11		S21		S12		S22	
	Mag	Ang	Mag	Ang	Mag	Ang	Mag	Ang
100	0.75	-114.9	12.22	61.1	0.007	108.3	0.81	-139.4
200	0.89	-147.6	3.94	32.2	0.038	111.4	0.92	-158.7
300	0.93	-161.9	2.08	20.9	0.065	102.5	0.95	-166.8
400	0.95	-173.3	1.17	14.0	0.095	94.7	0.97	-173.1
500	0.96	179.4	0.81	11.8	0.120	89.5	0.98	-177.0
600	0.96	172.0	0.57	12.5	0.150	84.2	0.98	179.2
700	0.96	166.5	0.46	15.4	0.176	80.3	0.98	176.5
800	0.96	161.3	0.39	19.7	0.202	76.6	0.97	174.0
900	0.95	155.4	0.35	25.5	0.233	72.3	0.97	171.2
1000	0.95	150.6	0.34	30.0	0.260	68.9	0.96	168.9

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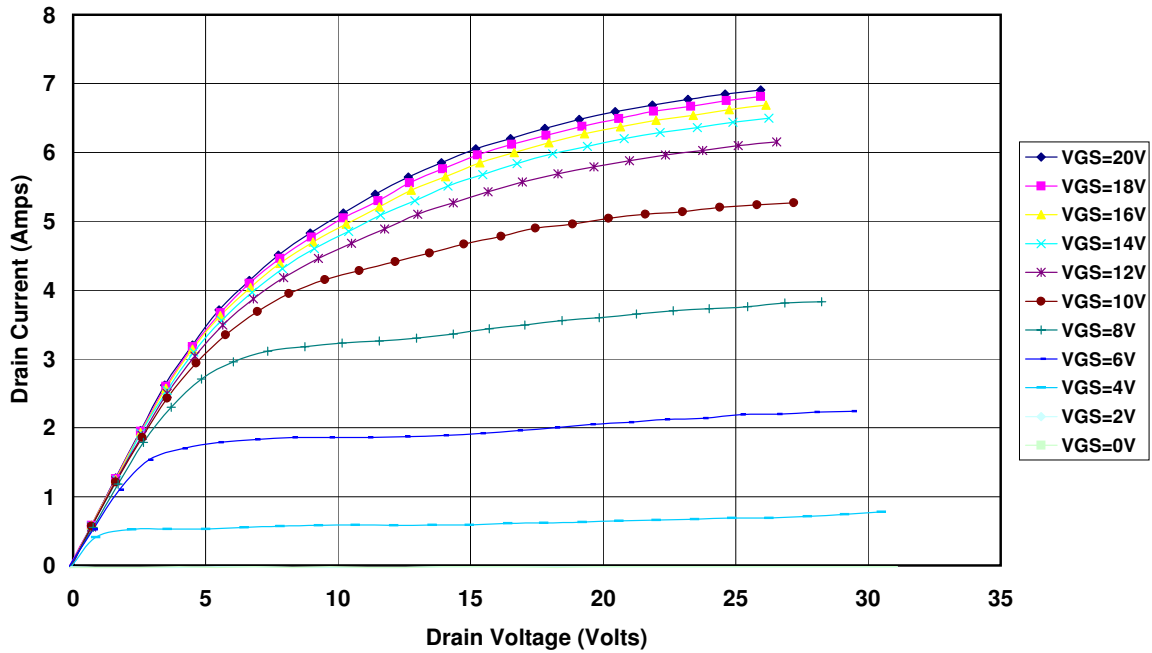


Figure 1 – Typical IV Characteristics.

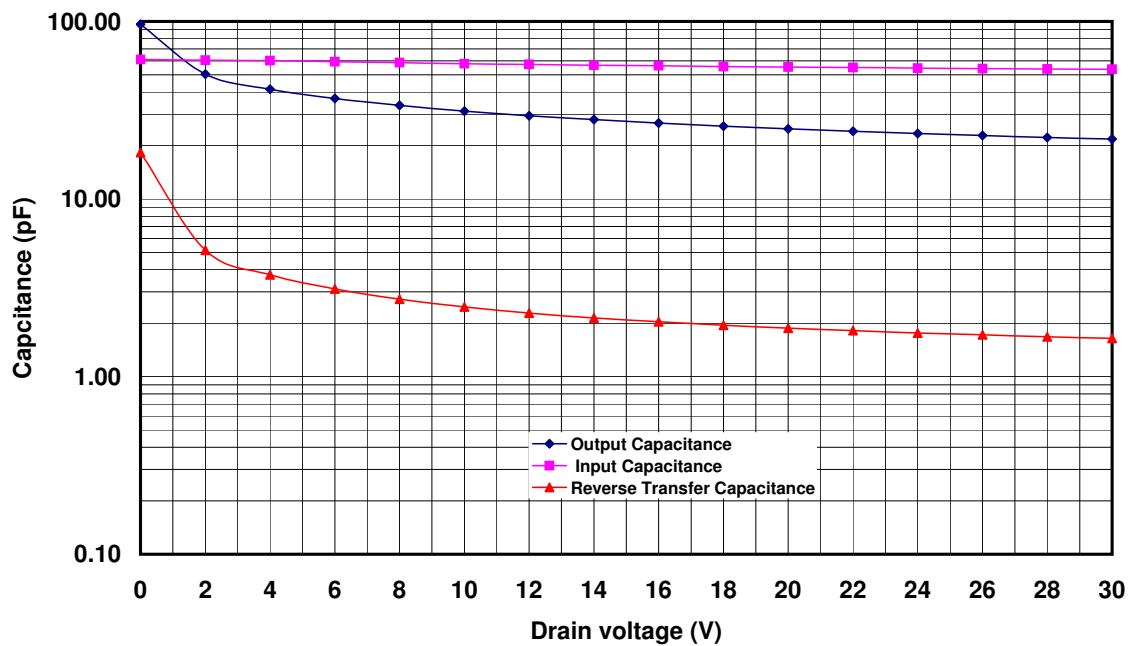
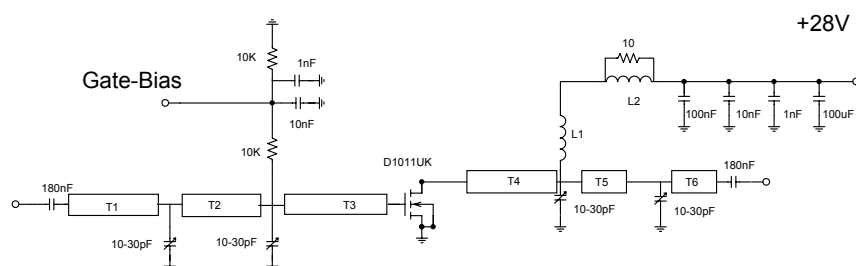


Figure 2 – Typical CV Characteristics.

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D1011UK 500MHz TEST FIXTURE

Substrate 1.6mm PTFE/glass, Er=2.5

All microstrip lines W=1.5mm

T1 22mm

T2 18mm

T3 18mm

T4 21mm

T5 22mm

T6 13mm

L1 6 turns 24swg enamelled copper wire, 6mm i.d.

L2 1.5 turns 24swg enamelled copper wire on a ferrite